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Abstract
Based on the exact resultant solution of two dimensional Poisson’s equation, a new two-dimensional model including surface channel potential, electric field, threshold voltage and subthreshold current for the fully depleted dual material gate (FDDMG) SOI MOSFET’s has been developed. The model is verified by the simulation results that agree well with those of the two-dimensional numerical simulator. Besides offering the physical insight into device physics, the model provides the basic designing guidance for the FD DMG SOI MOSFET’s
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